

Application No.: 09/998,134
Art Unit 2823

Attorney Docket No. 2332-0117P
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IN THE SPECIFICATION

Please replace the paragraph beginning on page 8, line 13, with the following rewritten paragraph:

B1
--As illustrated in Figures 3 and 4, in order to perform the ion implantation below gate patterns 13, a first halo implant process 25 is performed at a tilt angle C of approximately 45° at one side of the NMOS region 21 in parallel to the photoresist film pattern 15. The tilt angle C represents the degree of variation of the ion implantation from a line-D drawn perpendicular to the substrate. Here, the first halo implant process 25 is performed with an energy of 20KeV and a dose of 4.0×10^{12} ions/cm².--

Please replace the paragraph beginning on page 9, line 9, with the following rewritten paragraph:

B2
--As shown in Figures 3 and 6, a third halo implant process 27 is vertically performed on the semiconductor substrate 11 at a tilt angle of approximately 0° . Here, the third halo implant process 27 is performed with an energy of 16KeV and a dose of 4×10^{12} ions/cm².--

IN THE CLAIMS

Please cancel claim 3 without prejudice or disclaimer to the subject matter contained therein.

Please amend the claims as follows: